*2006 SEMATECH Litho Forum May 24 2006 @Vancouver*

Chemistry with a heart TOKUYAMA

# High-Index Fluoride Single Crystal for 193 nm Immersion Lithography


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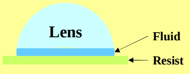
## Motivation

**High Refractive Index Material (HIM) is required for Hyper-NA 193nm Immersion Lithography in 2 Years!**

**Resolution = k1 (factor) × λ(193nm) / NA**

**NA = n × sinθ  where n : refractive index**

**'n' is restricted by minimum ($n_{lens}$, $n_{fluid}$, $n_{resist}$)**




**Candidates for HIM (our impression)**

| | Refractive Index | IBR | Melting Point [℃] | Size (Thickness) | Transmittance / Laser Durability |
|---|---|---|---|---|---|
| Oxide crystals | High | poor | 1900~ | middle | poor |
| Oxide ceramics | High | good | - | poor | poor |
| Fluoride crystals | Low-Middle | middle | 800~1400 | good | good? |

## Concept of Tokuyama

- **Core Technology**
  - Czochralski Method
  - Large Diameter
  - Fluoride Single Crystal

Original CZ Furnace    Φ300mm $CaF_2$ Single Crystal

- **Goal**
  - Develop High Index Fluoride Single Crystal

    **$BaLiF_3$($n_{193}$=1.64) Φ150 × > t50 <100>**

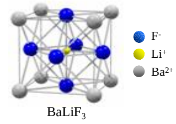
  - Develop Large Diameter <100> $CaF_2$ for IBR Compensation

    **$CaF_2$ Φ300× > t50 <100>**

## Basic Property of $BaLiF_3$

| | $CaF_2$ | LiF | $BaF_2$ | $BaLiF_3$ |
|---|---|---|---|---|
| Crystal structure | cubic | cubic | cubic | cubic |
| Lattice constant [Å] | 5.462 | 4.028 | 6.196 | 3.995 |
| Melting point [℃] | 1460 | 870 | 1355 | 880 |
| Density [g/cm³] | 3.18 | 2.64 | 4.89 | 5.28 |
| Refractive Index @193nm | 1.50 | 1.44 | 1.58 | 1.64 |
| IBR @193nm [nm/cm] | -3.4 | n.a. | 19.0 | 25.4 |

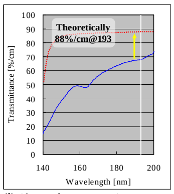
$BaLiF_3$ <100> Φ120×t100



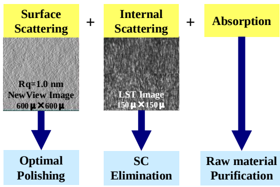

$BaLiF_3$

## Critical Issue of $BaLiF_3$ as of SPIE2006

| | Orient -ation | Refractive Index | IBR [nm/cm] | dn/dt | $A_{10}$ [1/cm] | SBR [nm/cm] | HG(-Z36) [ppb] | Size [mm] |
|---|---|---|---|---|---|---|---|---|
| Target | <100> | >1.7 | <10 | | <0.01 | <1 | | Φ150×t50 |
| $BaLiF_3$ | <100> | 1.64 | +25.4 | -2.3×$10^{-5}$ | ~0.15 | 0.6 | n.a. | Φ120×t100 |
| $CaF_2$ | <100> | 1.50 | -3.4 | -2.9×$10^{-5}$ | 0.0005 | 0.6 | 20-40 | Φ250×t50 |

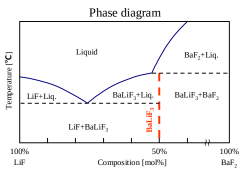



※without surface compensation

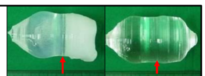



## Results of Crystal Growth by CZ method

**$BaLiF_3$ melts incongruently!**
**⇒ It can not be grown from stoichiometric melt composition.**



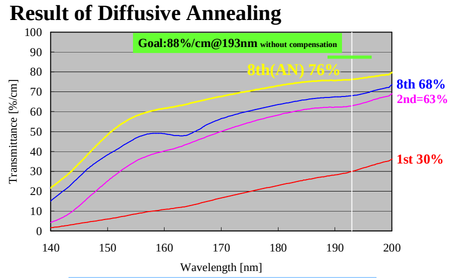

| Melt comp. Li:Ba | Obtained crystal |
|---|---|
| 50:50 | Never eutectic |
| 53:47 | Partial eutectic |
| 55:45 | Relatively clear |
| 57:43 | Milky ~Clear |



| Growth Condition | | |
|---|---|---|
| Pulling speed [mm/hr] | 1.0 →2.0 | 1.0 → 0.5 |
| Cooling rate [hr] | 60 | 4 |

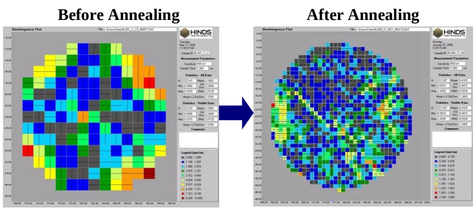
**Results**
**Melt composition :Li Rich**
**Pulling speed: Slow**
**Cooling rate: Fast**

## Result of Diffusive Annealing




**Result**
**Transmittance was improved by annealing process!**

## Stress Birefringence at 633nm

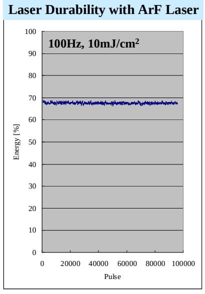



| Before Annealing | After Annealing |
|---|---|
| RMS=3.57nm/cm | RMS: 0.63nm/cm |
| MAX=9.26nm/cm | MAX:1.97nm/cm |

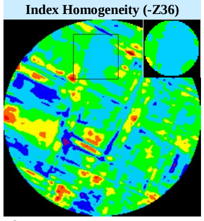
CA=Φ50mm

## Some Preliminary Results

**Laser Durability with ArF Laser**



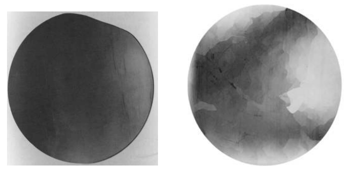

**Index Homogeneity (-Z36)**



Δ$n_{Φ45}$ PV=16ppm rms=1.7ppm

Δ$n_{Φ10}$ PV=4.9ppm rms=0.8ppm

## Crystallinity



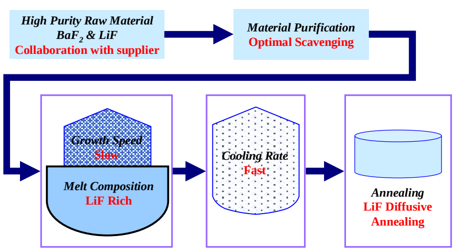
$BaLiF_3$ by CZ    $CaF_2$ by CZ

**No sub-grain structure was observed**

**Possibility of good index homogeneity**

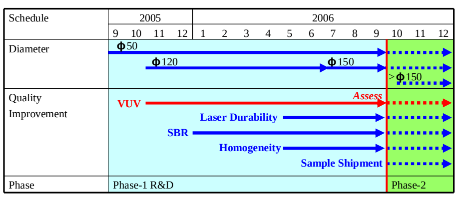
CA=Φ100mm

## Development Concept for Transmittance Improvement




## Optical Property Up-date & Schedule

| | Orient -ation | Refractive Index | IBR [nm/cm] | dn/dt | $A_{10}$ [1/cm] | SBR [nm/cm] | HG(-Z36) [ppm] | Size [mm] |
|---|---|---|---|---|---|---|---|---|
| Target | (100) | >1.7 | <10 | | <0.01 | <1 | 0.02 | Φ150×t50 |
| $BaLiF_3$ | (100) | 1.64 | +25.4 | -2.3×$10^{-5}$ | 0.067 | 0.6 | ~1 | Φ120×t100 |




## Conclusion

- Tokuyama try to manufacture $BaLiF_3$ as HIM and large <100> $CaF_2$ for IBR compensation.
- Critical issue of $BaLiF_3$ is transmittance.
  Champion: 0.067 [1/cm] / 85 [%/cm]  *Compensated data
- Cause of transmittance debasement might be mainly due to scattering of LiF precipitation.
- Transmittance could be improved by way of optimal growth condition and special annealing process.
- Tokuyama will try to improve transmittance and assess possibility of $BaLiF_3$ by the end of September.